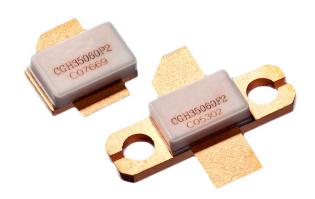


# CGH35060F2/P2

60 W, 3.1 - 3.5 GHz, 28 V, GaN HEMT

#### **Description**

The CGH35060F2/P2 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH35060F2/P2 ideal for 3.1 - 3.5 GHz S-band pulsed amplifier applications. The transistor is supplied in a ceramic/metal flange and pill package.



Package Types: 440193 & 440206 PNs: CGH35060F2 & CGH35060P2

#### Typical Performance Over 3.1-3.5 GHz (T<sub>c</sub> = 25°C) of Demonstration Amplifier

Parameter	3.1 GHz	3.3 GHz	3.5 GHz	Units
Small Signal Gain	12.0	13.2	11.5	dB
P <sub>OUT</sub> @ P <sub>IN</sub> = 36.5 dBm	47.0	47.6	46.7	dBm
Gain @ P <sub>IN</sub> = 36.5 dBm	10.4	11.06	10.1	dB
Drain Efficiency @ P <sub>IN</sub> = 36.5 dBm	55.0	62.0	62.0	%
Input Return Loss	-7.3	-17.0	-4.3	dB

Measured in the CGH35060F2-AMP amplifier circuit, under 100µs Pulse Width, 20% Duty Cycle and 28 V.

#### **Features**

- 3.1 3.5 GHz Operation
- 60 W Peak Power Capability
- 12 dB Small Signal Gain
- 60% Drain Efficiency







## Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V <sub>DSS</sub>	120	V	25°C
Gate-to-Source Voltage	V <sub>GS</sub>	-10, +2	V	25 C
Storage Temperature	T <sub>STG</sub>	-55, +150	°C	
Operating Junction Temperature	Tυ	225	- 1	
Maximum Forward Gate Current	I <sub>GMAX</sub>	14.4	mA	- 25°C
Maximum Drain Current <sup>1</sup>	I <sub>DMAX</sub>	6	Α	25 C
Soldering Temperature <sup>2</sup>	Ts	245	°C	
Screw Torque	τ	40	in-oz	
Thermal Resistance, Junction to Case, Pulsed <sup>3</sup>	R <sub>θJC</sub>	1.67	°C/W	85°C, Pulse Width = 300%, Duty Cycle = 10%
Case Operating Temperature <sup>3</sup>	T <sub>C</sub>	-40, +150	°C	

#### Notes

### **Electrical Characteristics (T<sub>c</sub> = 25°C)**

Characteristics	Symbol	Min.	Тур.	Max.	Units	Conditions
DC Characteristics <sup>1</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 14.4 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	V <sub>DC</sub>	V <sub>DS</sub> = 28 V, I <sub>D</sub> = 200 mA
Saturated Drain Current	I <sub>DS</sub>	10.1	14.0	-	Α	$V_{DS} = 6.0 \text{ V}, V_{GS} = 2 \text{ V}$
Drain-Source Breakdown Voltage	V <sub>BR</sub>	84	-	-	V <sub>DC</sub>	V <sub>GS</sub> = -8 V, I <sub>D</sub> = 14.4 mA
RF Characteristics <sup>2,3</sup> ( $T_c = 25^{\circ}C$ , $F_0 =$	3.3 GHz ur	iless oth	erwise n	oted)		
Small Signal Gain	Gss	11.0	13.0	-	dB	V <sub>DD</sub> = 28 V, I <sub>DQ</sub> = 200 mA
Drain Efficiency⁴	η	40	62	-	%	V - 20 V I - 200 mA B - 26 F W
Power Output⁴	Роит	45.6	47.6	-	dBm	$V_{DD} = 28 \text{ V}, I_{DQ} = 200 \text{ mA}, P_{IN} = 36.5 \text{ W}$
Output Mismatch Stress	VSWR			10:1	Ψ	No damage at all phase angles, $V_{DD} = 28 \text{ V}$ , $I_{DQ} = 200 \text{ mA}$ , $P_{OUT} = 60 \text{ W}$ Pulse
Dynamic Characteristics						
Input Capacitance	C <sub>GS</sub>	-	19.0	_		
Output Capacitance	C <sub>DS</sub>		5.9	_	pF	$V_{DS} = 28 \text{ V}, V_{GS} = -8 \text{ V}, f = 1 \text{ MHz}$
Feedback Capacitance	$C_{\sf GD}$	_	0.8	-		

#### Notes:

<sup>&</sup>lt;sup>1</sup> Current limit for long term, reliable operation

<sup>&</sup>lt;sup>2</sup> Refer to the Application Note on soldering

 $<sup>^{3}</sup>$  Measured for the CGH35060F2 at  $P_{DISS} = 57.6$  W.

<sup>&</sup>lt;sup>1</sup> Measured on wafer prior to packaging.

<sup>&</sup>lt;sup>2</sup> Measured in the CGH35060F2-AMP test fixture

<sup>&</sup>lt;sup>3</sup> 100μs Pulse Width at 20% Duty Cycle

 $<sup>^{4}</sup>$  Drain Efficiency =  $P_{OUT} / P_{DC}$ 



#### **Typical Performance**

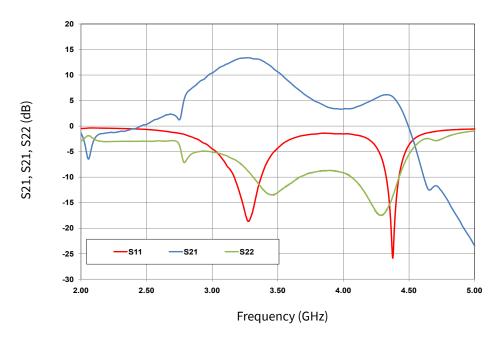
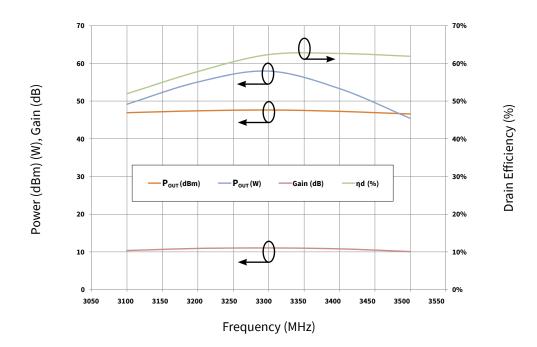


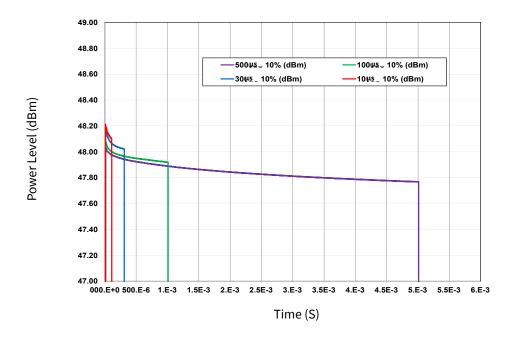
Figure 1. Small Signal Gain and Return Losses vs Frequency of the CGH35060F2 and CGH35060P2  $V_{DD}$  = 28 V,  $I_{DO}$  = 200 mA



**Figure 2.** Output Power, Gain and Drain Efficiency vs Frequency of the CGH35060F2 and CGH35060P2  $V_{DD}$  = 28 V,  $I_{DQ}$  = 200 mA, Pulse Width = 100 $\mu$ sec, Duty Cycle = 20%



#### **Typical Pulse Droop Performance**



## **Typical Performance**

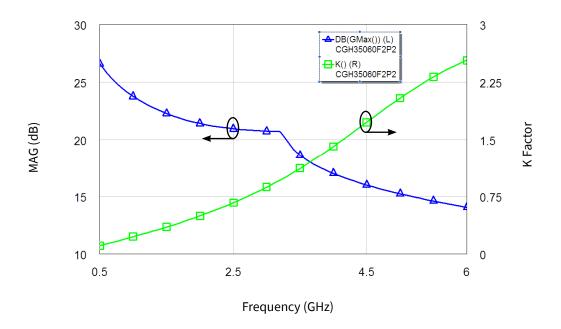
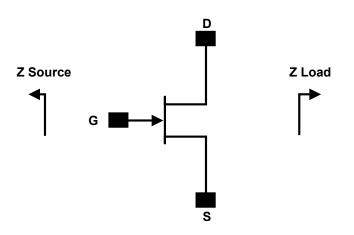


Figure 3. Simulated Maximum Available Gain and K Factor of the CGH35060F2 and CGH35060P2  $V_{DD}=28~V,~I_{DO}=200~mA$ 



#### **Source and Load Impedances**



Frequency (MHz)	Z Source	Z Load
3100	3.6 – j13.5	8.0 – j8.5
3200	3.6 - j12.8	7.1– j7.7
3300	3.5 – j12.1	6.5 – j6.8
3400	3.5 – j11.4	6.0 – j5.9
3500	3.3 – j10.7	5.6 – j5.1

#### **Electrostatic Discharge (ESD) Classifications**

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	НВМ	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 C101-C

 $<sup>^{1}</sup>$  V<sub>DD</sub> = 28V, I<sub>DQ</sub> = 200mA in the 440193 package  $^{2}$  Impedances are extracted from the CGH35060F2-AMP demonstration amplifier and are not source and load pull data derived from the transistor

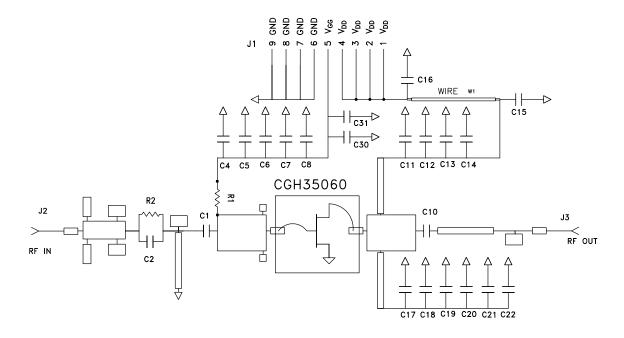


#### **CGH35060F2-AMP Demonstration Amplifier Circuit Bill of Materials**

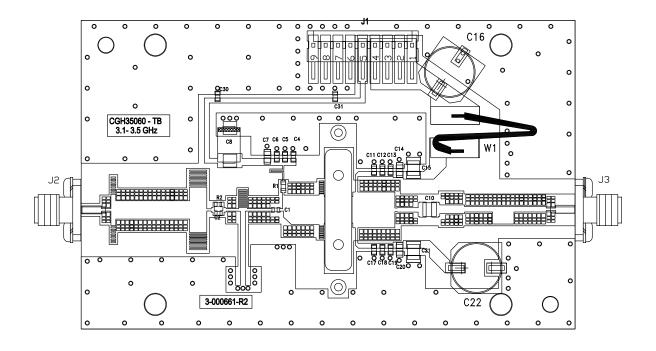
Designator	Description	Qty
R1	RES, 1/16 W, 0603, 1%, 5.1 OHMS	1
R2	RES, 1/16 W, 0603, 1%, 100 OHMS	1
C6, C13, C19	CAP, 470pF, +/-5%, 100 V, 0603	3
C16, C22	CAP, 33μF 100 V ELECT FK SMD	2
C15, C21	CAP, CER 1.0μF, 100 V, 10%, X7R 1210	2
C8	CAP, 10μF 16V SMT TANTALUM	1
C10	CAP, 20.0pF, +/-5%, 0603, ATC 100B	1
C1	CAP, 5.1pF, +/-5%, 0603, ATC 600S	1
C2	CAP, 3.0pF, +/-0.1pF, 0603, ATC 600S	1
C5, C12, C18, C30, C31	CAP, 4.7pF, 5%pF, 0603, ATC	5
C4, C11, C17	CAP, 7.5pF, 0.1pF, 0603, ATC	3
C7, C14, C20	CAP CER 33000pF, 0805, 100V, X7R	3
	РСВ	1
	BASEPLATE	1
J2, J3	CONN, SMA, PANEL MOUNT JACK	2
J1	HEADER RT>PLZ .1CEN LK 9POS	1
	2-56 SOC HD SCREW 1/4 SS	4
	#2 SPLIT LOCKWASHER SS	4
W1	WIRE, BLACK, 22 AWG ~ 2.0"	1
Q1	CGH35060F2	1



#### **CGH35060F2-AMP Demonstration Amplifier Circuit Schematic**



## **CGH35060F2-AMP Demonstration Amplifier Circuit Outline**





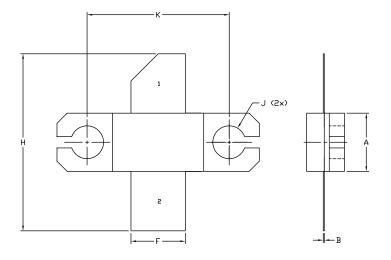
# Typical Package S-Parameters for CGH35060F2/P2, (Small Signal, $V_{DS}$ = 28 V, $I_{DQ}$ = 200 mA, angle in degrees)

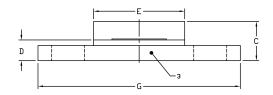
Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.927	-170.09	7.16	79.27	0.016	-6.59	0.596	-168.07
600 MHz	0.928	-172.55	5.95	75.10	0.016	-9.91	0.605	-168.34
700 MHz	0.929	-174.46	5.08	71.25	0.015	-12.90	0.615	-168.44
800 MHz	0.930	-176.04	4.42	67.64	0.015	-15.66	0.626	-168.49
900 MHz	0.931	-177.39	3.91	64.20	0.015	-18.24	0.637	-168.54
1.0 GHz	0.932	-178.59	3.50	60.90	0.015	-20.65	0.648	-168.63
1.1 GHz	0.933	-179.70	3.16	57.72	0.015	-22.94	0.659	-168.78
1.2 GHz	0.935	179.27	2.88	54.66	0.014	-25.10	0.670	-168.99
1.3 GHz	0.936	178.29	2.65	51.70	0.014	-27.14	0.681	-169.25
1.4 GHz	0.937	177.34	2.45	48.83	0.014	-29.08	0.692	-169.58
1.5 GHz	0.938	176.41	2.28	46.04	0.013	-30.91	0.702	-169.96
1.6 GHz	0.939	175.49	2.13	43.33	0.013	-32.65	0.712	-170.40
1.7 GHz	0.940	174.57	2.00	40.70	0.013	-34.29	0.721	-170.87
1.8 GHz	0.941	173.65	1.88	38.13	0.013	-35.85	0.730	-171.39
1.9 GHz	0.942	172.73	1.78	35.62	0.012	-37.32	0.738	-171.94
2.0 GHz	0.943	171.79	1.69	33.16	0.012	-38.70	0.746	-172.53
2.1 GHz	0.943	170.83	1.62	30.76	0.012	-40.01	0.753	-173.14
2.2 GHz	0.944	169.85	1.55	28.40	0.012	-41.25	0.760	-173.78
2.3 GHz	0.944	168.85	1.49	26.07	0.012	-42.41	0.766	-174.44
2.4 GHz	0.944	167.82	1.44	23.78	0.011	-43.51	0.772	-175.12
2.5 GHz	0.945	166.75	1.39	21.52	0.011	-44.55	0.777	-175.82
2.6 GHz	0.944	165.64	1.35	19.27	0.011	-45.52	0.781	-176.54
2.7 GHz	0.944	164.49	1.32	17.03	0.011	-46.44	0.785	-177.27
2.8 GHz	0.944	163.29	1.29	14.80	0.011	-47.31	0.789	-178.03
2.9 GHz	0.943	162.03	1.26	12.57	0.011	-48.13	0.792	-178.80
3.0 GHz	0.943	160.71	1.24	10.34	0.010	-48.92	0.795	-179.59
3.2 GHz	0.941	157.85	1.22	5.80	0.010	-50.38	0.798	178.78
3.4 GHz	0.938	154.62	1.21	1.13	0.010	-51.75	0.800	177.06
3.6 GHz	0.934	150.94	1.21	-3.76	0.010	-53.09	0.800	175.23
3.8 GHz	0.928	146.65	1.24	-8.97	0.010	-54.51	0.798	173.28
4.0 GHz	0.921	141.58	1.28	-14.63	0.011	-56.12	0.794	171.18
4.2 GHz	0.911	135.46	1.35	-20.90	0.011	-58.11	0.787	168.89
4.4 GHz	0.897	127.93	1.45	-28.01	0.012	-60.71	0.777	166.35
4.6 GHz	0.880	118.44	1.57	-36.26	0.012	-64.27	0.764	163.51
4.8 GHz	0.857	106.23	1.73	-46.04	0.014	-69.22	0.746	160.26
5.0 GHz	0.828	90.20	1.93	-57.83	0.015	-76.13	0.723	156.46
5.2 GHz	0.796	69.08	2.15	-72.17	0.017	-85.57	0.692	151.91
5.4 GHz	0.770	42.01	2.35	-89.39	0.018	-97.96	0.649	146.29
5.6 GHz	0.766	10.14	2.48	-109.22	0.019	-113.08	0.590	139.24
5.8 GHz	0.793	-22.34	2.47	-130.55	0.020	-129.85	0.509	130.26
6.0 GHz	0.839	-50.86	2.33	-152.01	0.019	-146.93	0.401	118.41

To download the s-parameters in s2p format, go to the CGH35060F2/P2 Product Page.



#### Product Dimensions CGH35060F2 (Package Type — 440193)





#### NOTES

1. DIMENSIONING AND TOLERANICING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020° BEYOND EDGE OF LID.

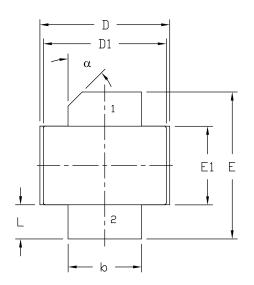
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008' IN ANY DIRECTION.

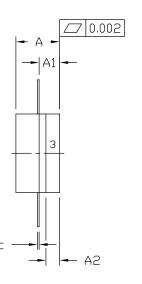
5. ALL PLATED SURFACES ARE NI/AU

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.225	0.235	5.72	5.97	
В	0.004	0.006	0.10	0.15	
С	0.145	0.165	3.68	4.19	
D	0.077	0.087	1.96	2.21	
E	0.355	0.365	9.02	9.27	
F	0.210	0.220	5.33	5.59	
G	0.795	0.805	20.19	20.45	
Н	0.670	0.730	17.02	18.54	
J	ø .130		3.30		
k	0.5	62	14.28		

PIN 1. GATE PIN 2. DRAIN PIN 3. SOURCE

# Product Dimensions CGH35060P2 (Package Type — 440206)





#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M 1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
- 4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008' IN ANY DIRECTION.

	INC	HES	MILLIM	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2x
С	0.004	0.006	0.10	0.15	2x
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
Е	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
L	0.085	0.115	2.16	2.92	2x
α	45°	REF	45°	REF	

- PIN 1. GATE
  - 2. DRAIN
  - 3. SOURCE



# **Product Ordering Information**

Order Number	Description	Unit of Measure	Image
CGH35060F2	GaN HEMT (Flanged)	Each	CCH OCO OCO N
CGH35060P2	GaN HEMT (Pill)	Each	CCH8508012
CGH35060F2-AMP	Test board with GaN HEMT installed	Each	



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